

## DIODE ARRAY PRODUCT SPECIFICATION

### MONOLITHIC AIR ISOLATED DIODE ARRAY

#### FEATURES:

- HERMETIC CERAMIC PACKAGE
- $B_v > 60V$  at  $10\mu A$
- $I_r < 100nA$  at  $40V$
- $C < 8.0$  pF

#### Absolute Maximum Ratings:

Symbol	Parameter	Limit	Unit
VBR(R)	*1 *2 Reverse Breakdown Voltage	60	Vdc
IO	*1 *3 Continuous Forward Current	300	mAdc
IFSM	*1 Peak Surge Current (tp= 1/120 s)	500	mAdc
PT1	*4 Power Dissipation per Junction @ 25 °C	400	mW
PT2	*4 Power Dissipation per Package @ 25 °C	500	mW
Top	Operating Junction Temperature Range	-65 to +150	°C
Tstg	Storage Temperature Range	-65 to +200	°C

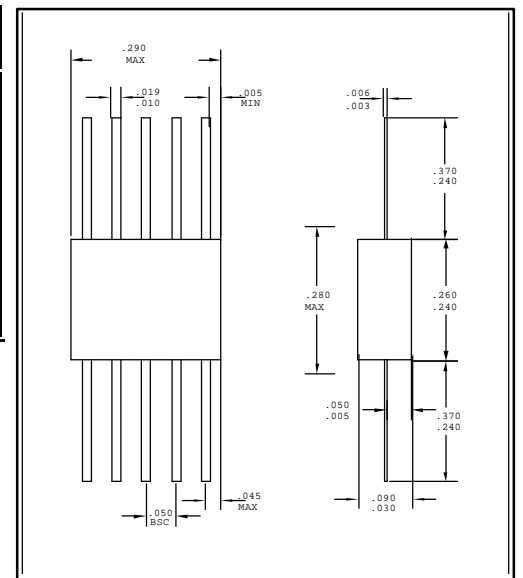
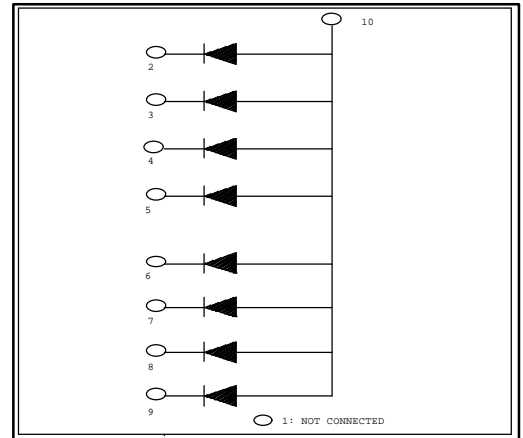
NOTE 1: Each Diode

NOTE 2: Pulsed: PW = 100ms max.; duty cycle  $\leq 20\%$

NOTE 3: Derate at  $2.4mA/^\circ C$  above  $+25^\circ C$

NOTE 4: Derate at  $4.0mW/^\circ C$  above  $+25^\circ C$

#### Electrical Characteristics (Per Diode) @ 25°C unless otherwise specified



#### PACKAGE OUTLINE

Symbol	Parameter	Conditions	Min	Max	Unit
Vf1	Forward Voltage	If = 100mAdc *1		1	Vdc
Vf2	Forward Voltage	If = 500mAdc *1		1.5	Vdc
IR1	Reverse Current	VR = 40 Vdc		0.1	uAdc
Ct	Capacitance (pin to pin)	VR = 0 Vdc, f = 1 MHz		8.0	pF
tfr	Forward Recovery Time	If = 500mAdc		40	ns
trr	Reverse Recovery Time	If = IR = 200mAdc, irr = 20mAdc, RL = 100 ohms		20	ns

NOTE 1: Pulsed: PW = 300us +/- 50us, duty cycle  $\leq 2\%$ , 90us after leading edge

Sertech reserves the right to make changes to any product design, specification or other information at any time without prior notice.